

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

MCH6431 — General-Purpose Switching Device Applications

Features

- ON-resistance RDS(on)1= $42m\Omega$ (typ.)
- · 4V drive
- · Halogen free compliance.

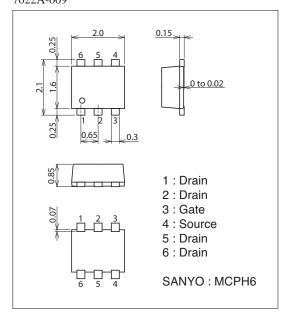
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		30	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		5	Α
Drain Current (Pulse)	IDP	PW≤10µs, duty cycle≤1%	20	Α
Allowable Power Dissipation	PD	When mounted on ceramic substrate (1200mm ² x0.8mm)	1.5	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Package Dimensions

unit : mm (typ) 7022A-009

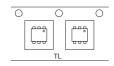


Product & Package Information

• Package : MCPH6

JEITA, JEDEC : SC-88, SOT-363
 Minimum Packing Quantity : 3,000 pcs./reel

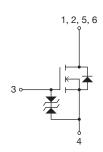
Packing Type: TL



Marking



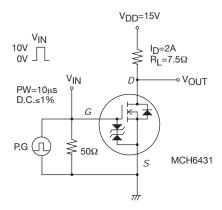
Electrical Connection

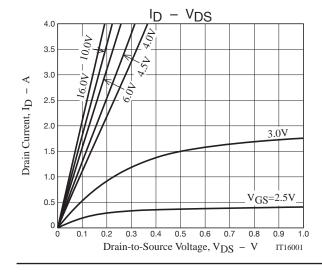


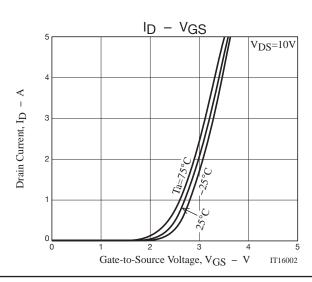
Electrical Characteristics at Ta=25°C

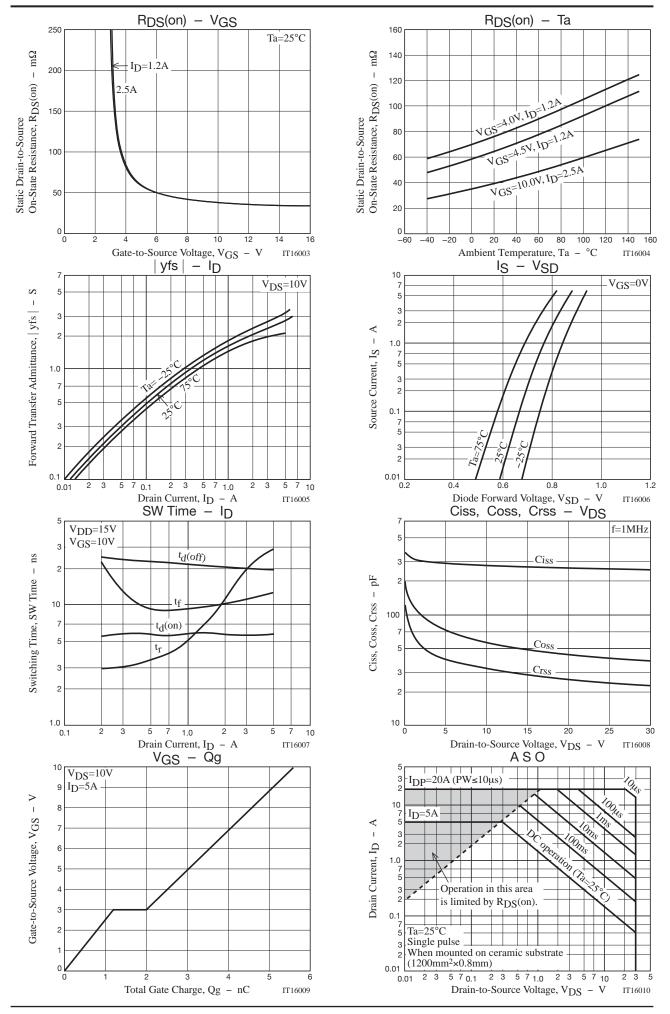
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	30			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =30V, V _{GS} =0V			1	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ
Cutoff Voltage	V _{GS} (off)	V _{DS} =10V, I _D =1mA	1.2		2.6	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =2.5A		2.2		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =2.5A, V _G S=10V		42	55	$m\Omega$
	R _{DS} (on)2	I _D =1.2A, V _G S=4.5V		65	91	$m\Omega$
	R _{DS} (on)3	I _D =1.2A, V _G S=4V		78	109	mΩ
Input Capacitance	Ciss	V _{DS} =10V, f=1MHz		280		pF
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		60		pF
Reverse Transfer Capacitance	Crss	V _{DS} =10V, f=1MHz		30		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.		5.7		ns
Rise Time	tr	See specified Test Circuit.		11		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		21		ns
Fall Time	tf	See specified Test Circuit.		10		ns
Total Gate Charge	Qg	V _{DS} =15V, V _{GS} =10V, I _D =5A		5.6		nC
Gate-to-Source Charge	Qgs	V _{DS} =15V, V _{GS} =10V, I _D =5A		1.2		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =15V, V _{GS} =10V, I _D =5A		0.8		nC
Diode Forward Voltage	V _{SD}	I _S =5A, V _{GS} =0V		0.85	1.2	V

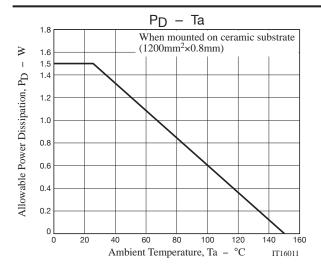
Switching Time Test Circuit











Note on usage: Since the MCH6431 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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